

## 产品规格书

## SPECIFICATIONS FOR PRODUCT

产品类型	TYPE	:	HC-49SMD
产品规格	SPEC	:	25MHz/49SMD/18PF/30PPM
产品型号	P/N	:	CJ03-250001830A30
日期	DATE	:	2020/08/02

核准及签名			部バ
R&D APPR.	SIGNATURED		DEPT.
拟制	审核	批准	频率器件事业部
ISSUE	CHECK	APPROVAL	
魏永鑫	许秋菊 2020/08/02	杨立新 2020/08/02	

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# HC-49/SMD Quartz Crystal

# CJ03-250001830A30

- 1. Scope:
- 1.1 This specification applies to the RoHS/SONY compliance quartz crystal unit with a frequency of 25MHz which will be used in crystal oscillator applications.
- 2. Construction:
- 2.1 Type of Quartz Resonator: HC-49/SMD

### 3. Electrical Characteristics

3.1 Nominal Frequency(f):	2	25MHz
3.2 Load Capacitance(C <sub>L</sub> ):	1	8pF
3.3 Frequency Tolerance(	∆f/f): ±	:30ppm
3.4 Frequency Temperatur	re Stability: ±	-30ppm
3.5 Resonance Resistance	e(ohm): 6	60ohms Max
3.6 Osc mode:	F	Fundamental mode
3.7 Shunt Capacitance(C <sub>0</sub> )	): <	<7pF
<ul><li>3.7 Shunt Capacitance(C<sub>0</sub>)</li><li>3.8 Drive Level(D<sub>L</sub>):</li></ul>		<7pF <300µW
	<	·
3.8 Drive Level(D <sub>L</sub> ):	e Range(T <sub>OPR</sub> ): -2	<300µW
<ul><li>3.8 Drive Level(D<sub>L</sub>):</li><li>3.9 Operating Temperature</li></ul>	e Range(T <sub>OPR</sub> ): -2 Range(T <sub>STG</sub> ): -4	≪300µW 20 to + 70°C

### 4. Reliability Specifications

This is the quality control and quality assurance and reliability tests performance data for the RoHS/

SONYcompliance 25MHz HC-49/SMD Quartz Crystal.

related to the specification and approval sheet provided by JSCJ.

Standard test condition (TEMP.: 20±5°C. Relative humidity: 65±20%)

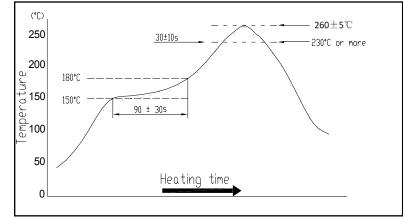
For any discrepancy in GO/NG, test will be done at TEMP.25±2°C, R.H. 65±5%.

NO.	PROCESS	SPECIFICATION	TEST METHOD
4.1	Temperature Cycle (GB/T 2423.22-2002, Method Nb)	Frequency change after test ≤± 5ppm.Resonance resistance change after test ≤10ohms.	10 cycles from -55°C to 125°C. Measurement taken after DUT being left at room temperature for 24±2 hours.
4.2	Low Temperature Storage (GB/T 2423.1-2001, Method Aa)	Frequency change after test ≤± 5ppm.Resonance resistance change after test ≤10ohms.	Spending 72 hrs at -55°C±3°C constant temperature. Measurement taken after DUT being left at room temperature for 24±2 hours.
4.3	High Temperature Storage (GB/T 2423.2-2001, Method Ba)	Frequency change after test ≤± 5ppm.Resonance resistance change after test ≤10ohms.	Spending 72 hrs at 125°C±3°C constant temperature. Measurement taken after DUT being left at room temperature for 24±2 hours.
4.4	Humidity (GB/T 2423.3- 2006, Method Cab)	Frequency change after test ≤± 5ppm.Resonance resistance change after test ≤10ohms.	Spending 96 hrs at 40 °C $\pm$ 3 °C, with 93 %R.H, Then keep the DUT in dry oven at 40 $\pm$ 5 °C for 24 hour. Measurement taken after DUT being left at room temperature for 1 to 2 hours.
4.5	Vibration (GB/T 2423.10- 1995, Method Fc)	Frequency change after test ≤± 5ppm.Resonance resistance change after test ≤10ohms.	Apply 0.75mm vibration at sweep frequency $10^{\sim}$ 500 Hz, 10 cycles in each direction of 3 axis. Measurement taken after 1 hour.
4.6	Shock (GB/T 2423.5-1995, Method Ea)	Frequency change after test ≤± 5ppm.Resonance resistance change after test ≤10ohms.and exhibit no visible damage.	Peak 1000m/s2, normal width 6ms half sine wave form, 3.7m/s, 3 perpendicular axis of samples, 3 cycles / direction, total 18 cycles. Measurement taken after 1 hour.
4.7	Drop (GB/T 2423.8-1995, Method Ed)	Frequency change after test ≤± 5ppm.Resonance resistance change after test ≤10ohms.and exhibit no visible damage.	Free drop to the steel plate with thickness of 3 mm from 0.75 m heights for 3 times.
4.8	Solderability (IEC60068-2- 58,Test Td:)	Terminals shall be covered more then 95% with solder.	Passed through the re-flow oven under the following condition. Preheat 150 to $180^{\circ}$ C for 60 to 120sec, and soldering time for $20s \pm 5s$ at $235^{\circ}$ C, peak soldering time for $10s \pm 1s$ betweein 240 and 250°C. There is no need to do functional test. 8-12X magnifier.
4.9	Terminal Strength (JIS-C- 6429 Method 1 & 2)	No visible damage	Mount on a glass-epoxy board (100x50x1.6mm), then bend to 2mm displacement (velocity 1mm/sec) and keep for 5 seconds. or pulling force 0.5kg for at least 60 seconds.
4.10	Resistance to Soldering Heat (IEC60068-2-58,Test Td: Table 4)	Frequency change after test ≤± 5ppm.Resonance resistance change after test ≤10ohms.	Passed through the re-flow oven under the following condition. Preheat 150 to 180°C for 60 to 120sec, and sodering time for 60s max at 235°C, peak soldering time for 20s max at 265°C max. Measurement taken after DUT being left at room temperature for at least 2 hours.
4.11	OTHERS		

5. Recommended Reflow soldering condition (SMD)

Solder profile

Peak: 260±5°C Soldering zone: 230°C or more, 30±10s. Pre-heating zone 1: 150 $\sim$  180°C, 90±30s



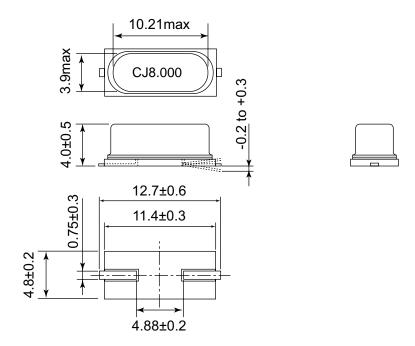
Temperature profile for reflow soldering

6. Soldering iron method

Bit temperature:  $350\pm10$  °C Application time of soldering iron:3+1 s. For other procedures, refer to IEC 60068-2-20.

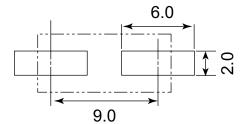
#### **Package Outline Dimensions**

#### Units:mm



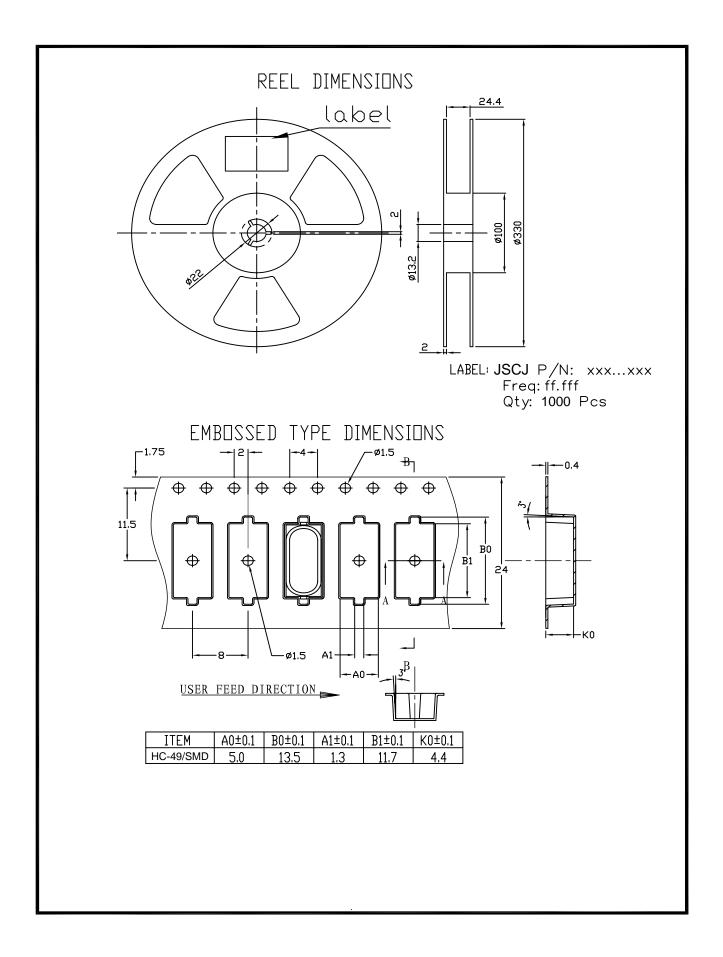
### Suggested Pad Layout

Units:mm



#### NOTICE

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